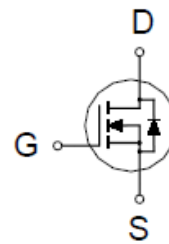
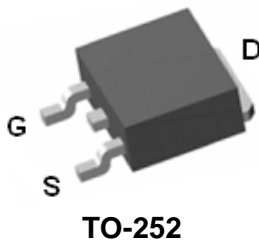


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PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	32m Ω @ $V_{GS} = 10V$	34A



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ¹	$T_C = 25\text{ }^\circ\text{C}$	I_D	34	A
	$T_C = 100\text{ }^\circ\text{C}$		22	
Pulsed Drain Current ²		I_{DM}	100	
Avalanche Current		I_{AS}	50	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	125	mJ
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	83	W
	$T_C = 100\text{ }^\circ\text{C}$		33	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		1.8	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		62.5	

¹Pulse width limited by maximum junction temperature.

²Limited by package

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

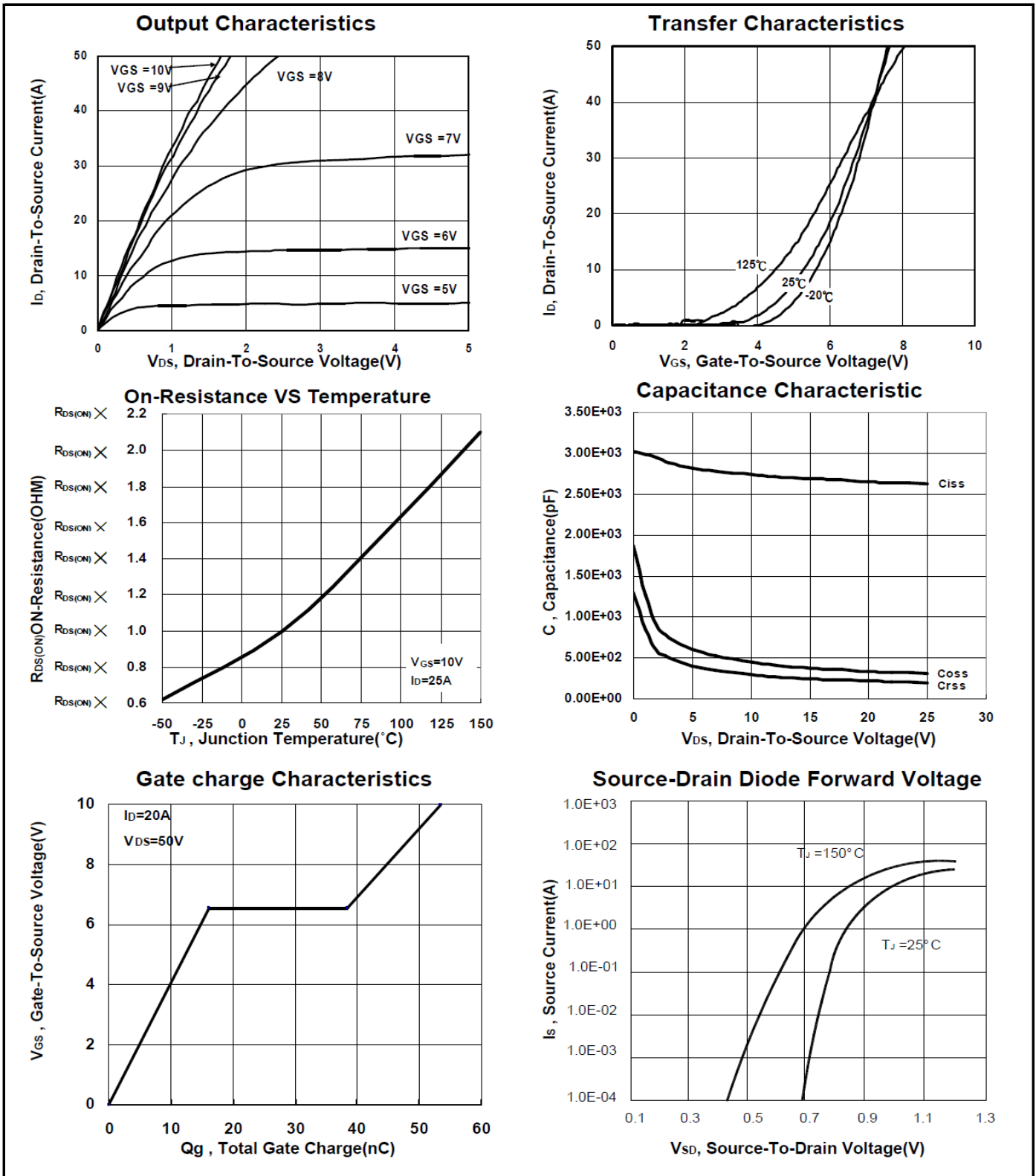
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.8	2.8	4.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V			1	μA
		V _{DS} = 80V, V _{GS} = 0V, T _J = 125 °C			10	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	100			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 25A		25	32	mΩ
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 25A		30		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		2700		pF
Output Capacitance	C _{oss}			307		
Reverse Transfer Capacitance	C _{rss}			205		
Total Gate Charge ²	Q _g	V _{DS} = 50V, V _{GS} = 10V, I _D = 25A		54		nC
Gate-Source Charge ²	Q _{gs}			16		
Gate-Drain Charge ²	Q _{gd}			23		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		2.5		Ω
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 50V, I _D ≅ 25A, V _{GS} = 10V, R _{GEN} = 6Ω		10		nS
Rise Time ²	t _r			10		
Turn-Off Delay Time ²	t _{d(off)}			15		
Fall Time ²	t _f			10		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I _S				34	A
Forward Voltage ¹	V _{SD}	I _F = 25A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 25A, dI _F /dt = 100A / μS		62		nS
Reverse Recovery Charge	Q _{rr}				175	

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

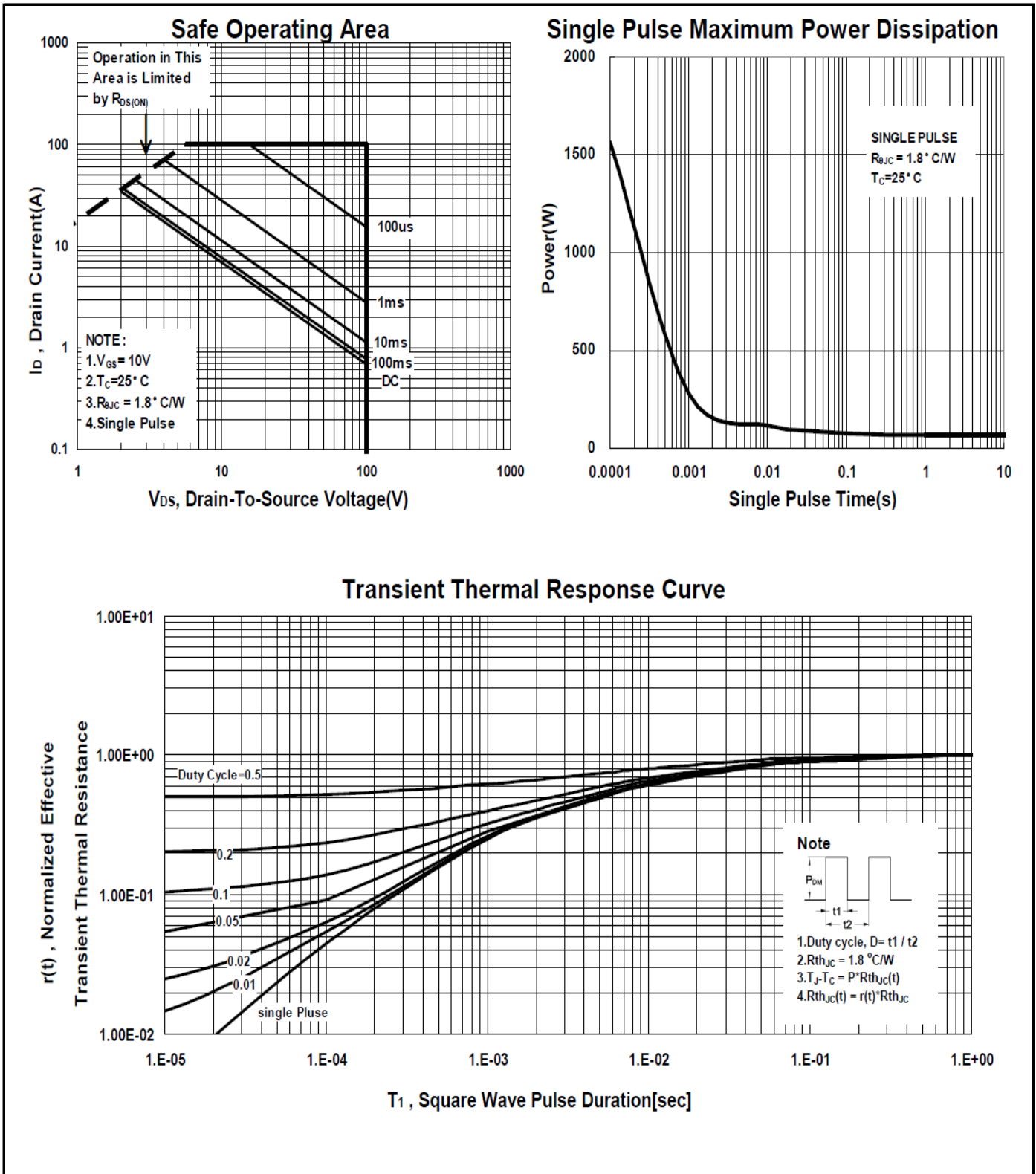
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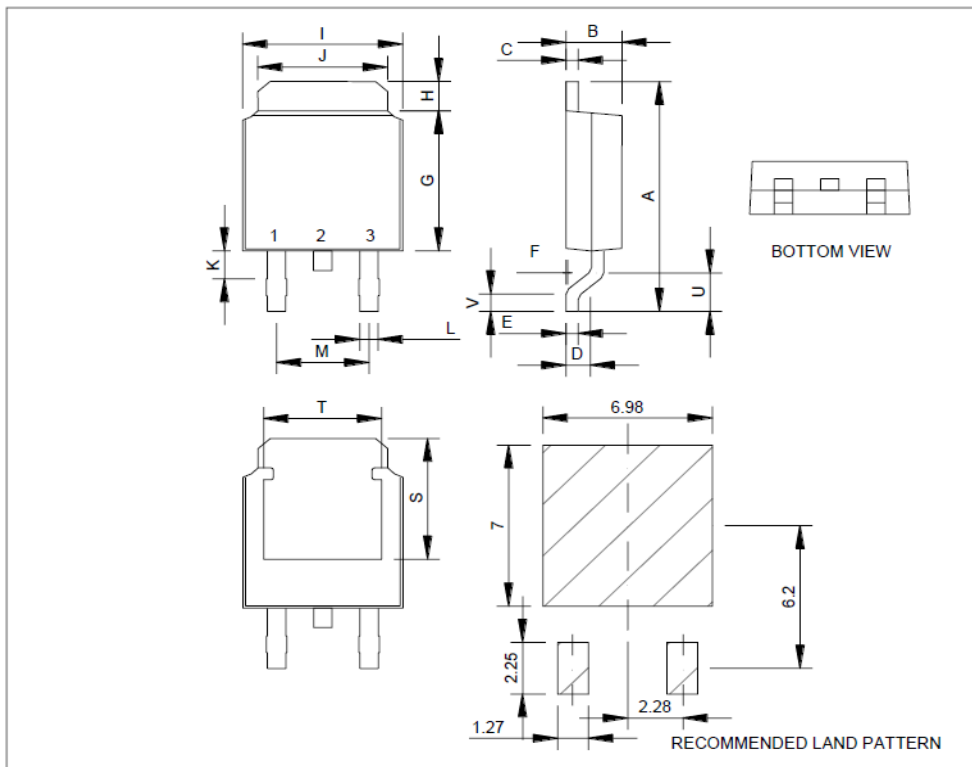
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Package Dimension

TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	8.9	10	10.41	J	4.8		5.64
B	2.1	2.2	2.4	K	0.15		1.1
C	0.4	0.5	0.61	L	0.4	0.76	0.89
D	0.82	1.2	1.5	M	4.2	4.58	5
E	0.4	0.5	0.61	S	4.9	5.1	5.3
F	0		0.2	T	4.6	4.75	5.44
G	5.3	6.1	6.3	U	1.4		1.78
H	0.9		1.7	V	0.55	1.25	1.7
I	6.3	6.5	6.8				



*因为各家封装模具不同而外观略有所差异，不影响电性及其Layout